

L1: (18) (US-4933743-5 or US-5824599-5 or US-6069088-5)
 L2: (180) farrar-paul-a.in.
 L3: (1384) substrate and (via or opening) and seed and b
 L4: (1382) 2 not (1 2)
 L5: (108) 4 and ("Hf" or hafnium) and ("Er" or titanium
 L6: (49) 5 and (polyimide or polymer)
 L7: (34) 6 and (etchS4 adj) (barrier or stop)
 L8: (15) 6 not 7
 L9: (10) ("5937320") or ("6103320") or ("6208016") or
 L10: (1) "20040217481"
 L11: (3) ("20050023688") or ("20040217481") or ("20050
 Failed
 Saved
 S1: (11) ("6436787") or ("6362812") or ("20020047153")
 S2: (0) ("6436787") or ("6362812") or ("20020047153")

Name: []
 Title: []
 Author: []
 Date: []
 Status: []
 Keywords: []
 Comments: []

| | U | I | PT | P | Document ID | Issue Date | Pages | Title | Current OR | Current X |
|----|--------------------------|--------------------------|--------------------------|--------------------------|----------------|------------|-------|---|------------|-----------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 6348751 | 20020219 | 16 | Copper interconnections with enhanced electromigration resistance and reduced defect sensitivity and method of forming same | 257/751 | 257/751 |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20030205823 | 20031106 | 13 | Method for improving nucleation and adhesion of CVD and ALD films deposited onto low-dielectric-constant dielectrics | 257/774 | 257/768 |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20040185923 | 20040923 | 52 | Monolithic fuel cell structure and method of manufacture | 429/38 | 204/252 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 2004023253 | 20040205 | 177 | Device structure for closely spaced electrodes | 435/6 | 429/35 |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20030124791 | 20030703 | 37 | Detection of Al ₂ O ₃ ears for process control in FeRAM processing | 438/238 | 205/777.5 |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20030119251 | 20030526 | 33 | Methods of preventing reduction of FeOx during PRT formation by metalorganic chemical vapor deposition or other processing | 438/239 | 435/267.2 |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 6713342 | 20040330 | 35 | FeRAM sidewall diffusion barrier etch | 438/239 | 257/221.0 |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 6686236 | 20040203 | 38 | Methods of preventing reduction of FeOx during PRT formation by metalorganic chemical vapor deposition or other processing | 438/239 | 438/239 |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20030143808 | 20030731 | 37 | FeRAM CAPACITOR POST STACK ETCH CLEAN/REPAIR | 438/240 | 257/221.0 |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 6492222 | 20021210 | 19 | Method of dry etching PRT capacitor stack to form high-density ferroelectric memory devices | 438/240 | 438/239 |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20040087037 | 20040506 | 15 | Etch-stop material for improved manufacture of magnetic devices | 438/3 | 438/250 |
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20030129771 | 20030710 | 37 | Method of forming an FeRAM capacitor having a bottom electrode diffusion barrier | 438/3 | 257/221.0 |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20030703 | 20030703 | 37 | Method of forming an FeRAM having a multi-layer hard mask and patterning | 438/3 | 257/221.0 |